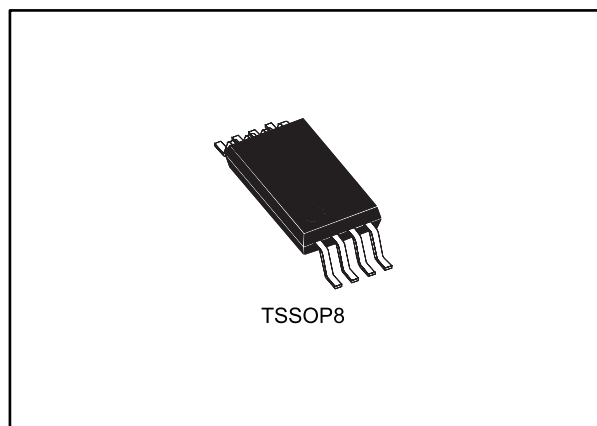


Low-power, dual operational amplifier

Datasheet - production data



Features

- Frequency compensation implemented internally
- Large DC voltage gain: 100 dB
- Wide bandwidth (unity gain): 1.1 MHz (temperature compensated)
- Very low supply current/amplifier, essentially independent of supply voltage
- Low input bias current: 20 nA (temperature compensated)
- Low input offset current: 2 nA
- Input common-mode voltage range includes negative rail
- Differential input voltage range equal to the power supply voltage
- Large output voltage swing
0 V to $(V_{CC+}) - 1.5$ V

Related products

- See LM2904WH for enhanced ESD performances

Description

This circuit consists of two independent, high gain operational amplifiers (op amps) that have frequency compensation implemented internally. They are designed specifically for automotive and industrial control systems. The circuit operates from a single power supply over a wide range of voltages. The low power supply drain is independent of the magnitude of the power supply voltage.

Application areas include transducer amplifiers, DC gain blocks and all the conventional op amp circuits which can now be more easily implemented in single power supply systems. For example, these circuits can be directly supplied from the standard 5 V which is used in logic systems and easily provides the required interface electronics without requiring any additional power supply.

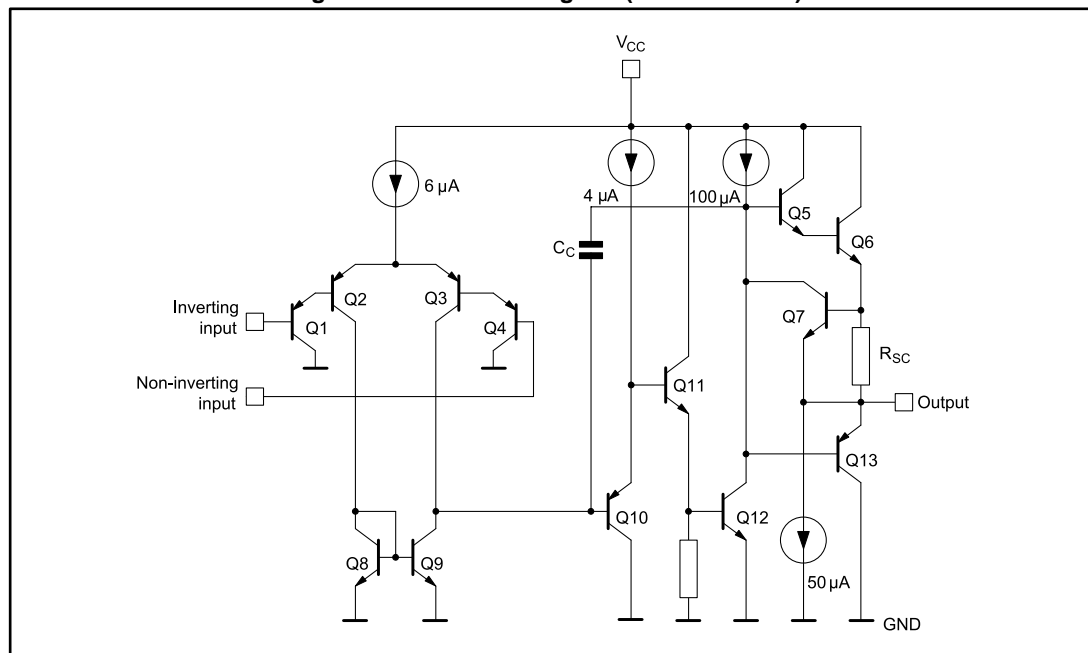
In the linear mode, the input common-mode voltage range includes ground and the output voltage can also swing to ground, even though operated from a single power supply.

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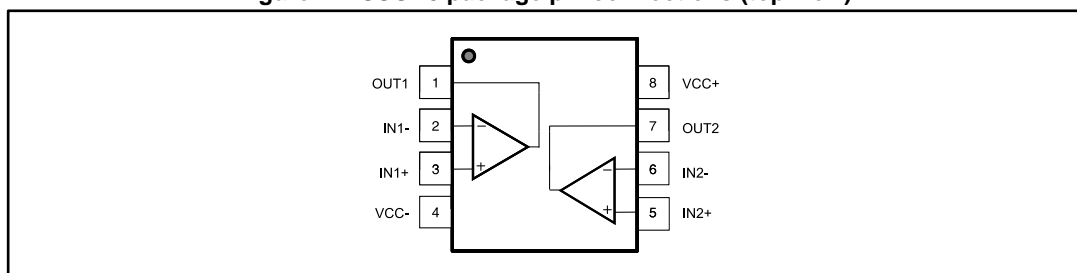
1 Schematic diagram

Figure 1: Schematic diagram (1/2 LM2904AH)



2 Package pin connections

Figure 2: TSSOP8 package pin connections (top view)



3 Absolute maximum ratings and operating conditions

Table 1: Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{CC}	Supply voltage ⁽¹⁾	±16 or 32	V
V_{id}	Differential input voltage ⁽²⁾	±32	
V_{in}	Input voltage	-0.3 to 32	
	Output short-circuit duration ⁽³⁾	Infinite	s
I_{in}	Input current: V_{in} driven negative ⁽⁴⁾	5 mA in DC or 50 mA in AC (duty cycle = 10 %, T = 1 s)	mA
	Input current: V_{in} driven positive above AMR value ⁽⁵⁾	0.4	
T_{stg}	Storage temperature range	-65 to 150	°C
T_j	Maximum junction temperature	160	
R_{thja}	Thermal resistance junction to ambient ⁽⁶⁾	120	°C/W
R_{thjc}	Thermal resistance junction to case ⁽⁶⁾	37	
ESD	HBM: human body model ⁽⁷⁾	300	V
	MM: machine model ⁽⁸⁾	200	
	CDM: charged device model ⁽⁹⁾	1.5	kV

Notes:

⁽¹⁾All voltage values, except differential voltage are with respect to network ground terminal.

⁽²⁾Differential voltages are the non-inverting input terminal with respect to the inverting input terminal.

⁽³⁾Short-circuits from the output to V_{CC} can cause excessive heating if (V_{CC+}) > 15 V. The maximum output current is approximately 40 mA, independent of the magnitude of V_{CC} . Destructive dissipation can result from simultaneous short-circuits on all amplifiers.

⁽⁴⁾This input current only exists when the voltage at any of the input leads is driven negative. It is due to the collector-base junction of the input PNP transistor becoming forward-biased and thereby acting as input diode clamp. In addition to this diode action, there is NPN parasitic action on the IC chip. This transistor action can cause the output voltages of the op amps to go to the V_{CC} voltage level (or to ground for a large overdrive) for the time during which an input is driven negative. This is not destructive and normal output is restored for input voltages above -0.3 V.

⁽⁵⁾The junction base/substrate of the input PNP transistor polarized in reverse must be protected by a resistor in series with the inputs to limit the input current to 400 μ A max ($R = (V_{in}-32 V)/400 \mu$ A).

⁽⁶⁾Short-circuits can cause excessive heating and destructive dissipation. Values are typical.

⁽⁷⁾Human body model: a 100 pF capacitor is charged to the specified voltage, then discharged through a 1.5 k Ω resistor between two pins of the device. This is done for all couples of connected pin combinations while the other pins are floating.

⁽⁸⁾Machine model: a 200 pF capacitor is charged to the specified voltage, then discharged directly between two pins of the device with no external series resistor (internal resistor < 5 Ω). This is done for all couples of connected pin combinations while the other pins are floating.

⁽⁹⁾Charged device model: all pins and the package are charged together to the specified voltage and then discharged directly to the ground through only one pin. This is done for all pins.

Table 2: Operating conditions

Symbol	Parameter	Value	Unit
V_{CC}	Supply voltage	3 to 30	V
V_{icm}	Common-mode input voltage range	0 to $(V_{CC+}) - 1.5$	
T_{oper}	Operating free-air temperature range	-40 to 150	°C

4 Electrical characteristics

Table 3: $V_{CC+} = 5\text{ V}$, $V_{CC-} = \text{ground}$, $V_O = 1.4\text{ V}$, $T_{\text{amb}} = 25\text{ }^\circ\text{C}$ (unless otherwise specified),
 $T_{\text{min}} = -40\text{ }^\circ\text{C}$, and $T_{\text{max}} = 150\text{ }^\circ\text{C}$

Symbol	Parameter	Min.	Typ.	Max.	Unit
V_{io}	Input offset voltage, $T_{\text{amb}} = 25\text{ }^\circ\text{C}$ ⁽¹⁾		1	2	mV
	Input offset voltage, $T_{\text{min}} \leq T_{\text{amb}} \leq T_{\text{max}}$ ⁽¹⁾			6	
$\Delta V_{io}/\Delta T$	Input offset voltage drift		7	40	$\mu\text{V}/^\circ\text{C}$
I_{io}	Input offset current, $T_{\text{amb}} = 25\text{ }^\circ\text{C}$		2	30	nA
	Input offset current, $T_{\text{min}} \leq T_{\text{amb}} \leq T_{\text{max}}$			40	
$\Delta I_{io}/\Delta T$	Input offset current drift		10	300	$\text{pA}/^\circ\text{C}$
I_{ib}	Input bias current, $T_{\text{amb}} = 25\text{ }^\circ\text{C}$ ⁽²⁾		20	150	nA
	Input bias current, $T_{\text{min}} \leq T_{\text{amb}} \leq T_{\text{max}}$ ⁽²⁾			200	
A_{vd}	Large signal voltage gain, $V_{CC+} = 15\text{ V}$, $R_L = 2\text{ k}\Omega$, $V_O = 1.4\text{ V}$ to 11.4 V , $T_{\text{amb}} = 25\text{ }^\circ\text{C}$	50	100		V/mV
	Large signal voltage gain, $V_{CC+} = 15\text{ V}$, $R_L = 2\text{ k}\Omega$, $V_O = 1.4\text{ V}$ to 11.4 V , $T_{\text{min}} \leq T_{\text{amb}} \leq T_{\text{max}}$	25			
SVR	Supply voltage rejection ratio ($R_S \leq 10\text{ k}\Omega$), $T_{\text{amb}} = 25\text{ }^\circ\text{C}$	65	100		dB
	Supply voltage rejection ratio ($R_S \leq 10\text{ k}\Omega$), $T_{\text{min}} \leq T_{\text{amb}} \leq T_{\text{max}}$	65			
I_{CC}	Supply current, all amp, no load, $T_{\text{amb}} = 25\text{ }^\circ\text{C}$, $V_{CC+} = 5\text{ V}$		0.7	1.2	mA
	Supply current, all amp, no load, $T_{\text{min}} \leq T_{\text{amb}} \leq T_{\text{max}}$, $V_{CC+} = 30\text{ V}$			2	
V_{icm}	Input common mode voltage range ($V_{CC+} = 30\text{ V}$), $T_{\text{amb}} = 25\text{ }^\circ\text{C}$ ⁽³⁾	0		(V_{CC+}) - 1.5	V
	Input common mode voltage range ($V_{CC+} = 30\text{ V}$), $T_{\text{min}} \leq T_{\text{amb}} \leq T_{\text{max}}$	0		(V_{CC+}) - 2	
CMR	Common-mode rejection ratio ($R_S = 10\text{ k}\Omega$), $T_{\text{amb}} = 25\text{ }^\circ\text{C}$	70	85		dB
	Common-mode rejection ratio ($R_S = 10\text{ k}\Omega$), $T_{\text{min}} = T_{\text{amb}} = T_{\text{max}}$	60			
I_{source}	Output short-circuit current, $V_{CC+} = 15\text{ V}$, $V_O = 2\text{ V}$, $V_{id} = 1\text{ V}$	20	40	60	mA
I_{sink}	Output sink current, $V_O = 2\text{ V}$, $V_{CC+} = 5\text{ V}$	10	20		
		Output sink current, $V_O = 0.2\text{ V}$, $V_{CC+} = 15\text{ V}$	12	50	μA
V_{OH}	High level output voltage ($V_{CC+} = 30\text{ V}$), $T_{\text{amb}} = 25\text{ }^\circ\text{C}$, $R_L = 2\text{ k}\Omega$	26			V
	High level output voltage ($V_{CC+} = 30\text{ V}$), $T_{\text{min}} \leq T_{\text{amb}} \leq T_{\text{max}}$	26	27		
	High level output voltage ($V_{CC+} = 30\text{ V}$), $T_{\text{amb}} = 25\text{ }^\circ\text{C}$, $R_L = 10\text{ k}\Omega$	27			
	High level output voltage ($V_{CC+} = 30\text{ V}$), $T_{\text{min}} \leq T_{\text{amb}} \leq T_{\text{max}}$	27	28		
V_{OL}	Low level output voltage ($R_L = 10\text{ k}\Omega$), $T_{\text{amb}} = 25\text{ }^\circ\text{C}$		5	20	mV
	Low level output voltage ($R_L = 10\text{ k}\Omega$), $T_{\text{min}} = T_{\text{amb}} = T_{\text{max}}$			20	
SR	Slew rate, $V_{CC+} = 15\text{ V}$, $V_{in} = 0.5$ to 3 V , $R_L = 2\text{ k}\Omega$, $C_L = 100\text{ pF}$, unity gain, $T_{\text{amb}} = 25\text{ }^\circ\text{C}$	0.3	0.6		$\text{V}/\mu\text{s}$
	Slew rate, $V_{CC+} = 15\text{ V}$, $V_{in} = 0.5$ to 3 V , $R_L = 2\text{ k}\Omega$, $C_L = 100\text{ pF}$, unity gain, $T_{\text{min}} = T_{\text{amb}} = T_{\text{max}}$	0.2			
GBP	Gain bandwidth product, $f = 100\text{ kHz}$, $V_{CC+} = 30\text{ V}$, $V_{in} = 10\text{ mV}$, $R_L = 2\text{ k}\Omega$, $C_L = 100\text{ pF}$	0.7	1.1		MHz

Symbol	Parameter	Min.	Typ.	Max.	Unit
THD	Total harmonic distortion, $f = 1 \text{ kHz}$, $A_V = 20 \text{ dB}$, $R_L = 2 \text{ k}\Omega$, $V_o = 2 \text{ V}_{pp}$, $C_L = 100 \text{ pF}$, $V_{CC+} = 30 \text{ V}$		0.02		%
e_n	Equivalent input noise voltage, $f = 1 \text{ kHz}$, $R_S = 100 \text{ }\Omega$, $V_{CC+} = 30 \text{ V}$		55		$\text{nV}/\sqrt{\text{Hz}}$
V_{O1}/V_{O2}	Channel separation, $1 \text{ kHz} \leq f \leq 20 \text{ kHz}$ ⁽⁴⁾		120		dB

Notes:

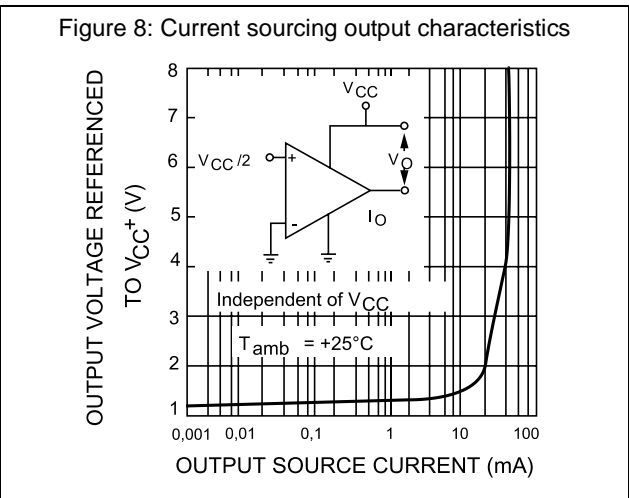
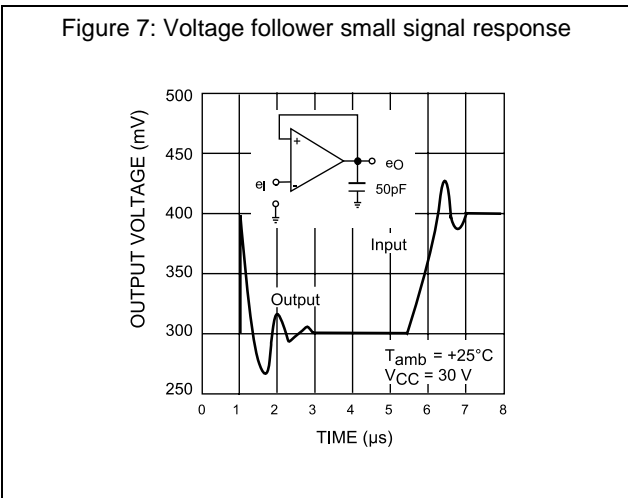
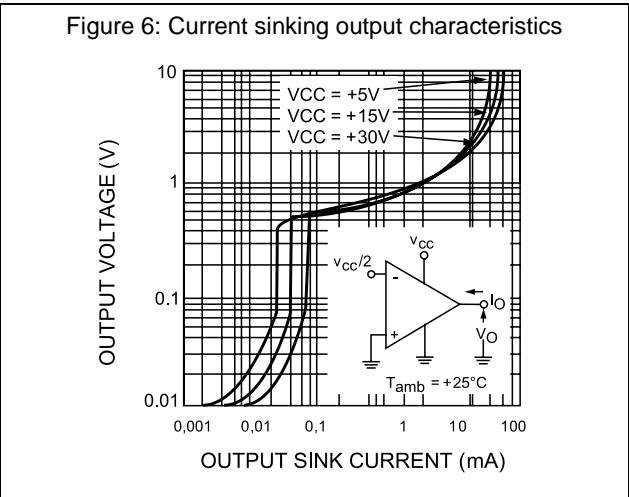
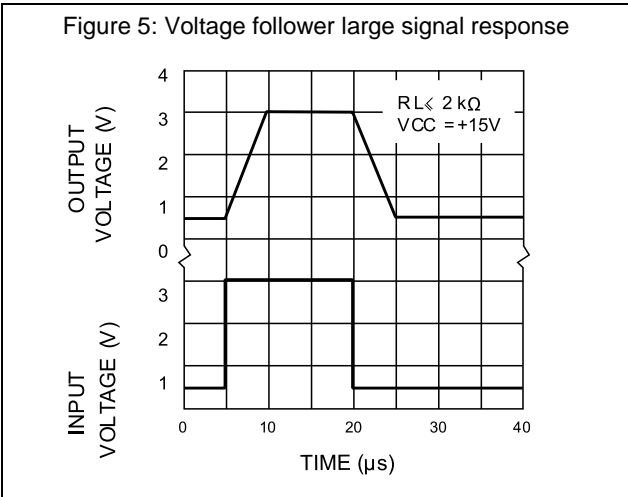
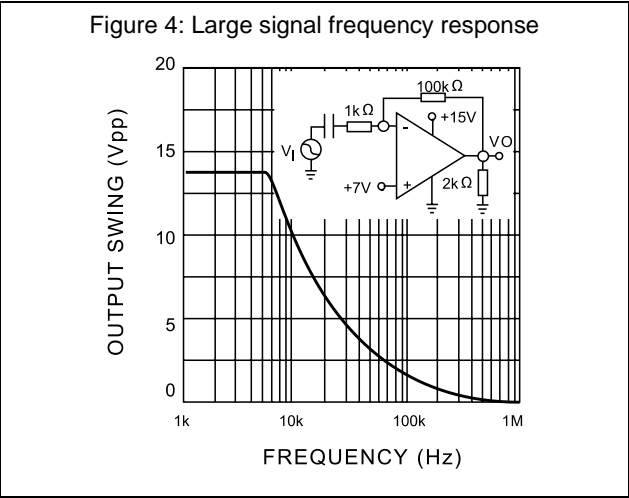
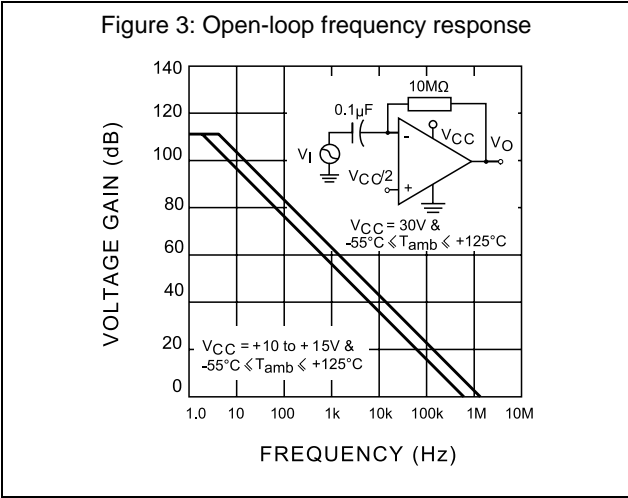
⁽¹⁾ $V_O = 1.4 \text{ V}$, $R_S = 0 \text{ }\Omega$, $5 \text{ V} < V_{CC+} < 30 \text{ V}$, $0 \text{ V} < V_{ic} < (V_{CC+}) - 1.5 \text{ V}$.

⁽²⁾ The direction of the input current is out of the IC. This current is essentially constant, independent of the state of the output, so there is no change in the loading charge on the input lines.

⁽³⁾ The input common-mode voltage of either input signal voltage should not be allowed to go negative by more than 0.3 V. The upper end of the common-mode voltage range is $(V_{CC+}) - 1.5 \text{ V}$, but either or both inputs can go to 32 V without damage.

⁽⁴⁾ Due to the proximity of external components, ensure that the stray capacitance does not cause coupling between these external parts. This can typically be detected at higher frequencies because this type of capacitance increases.

5 Electrical characteristic curves



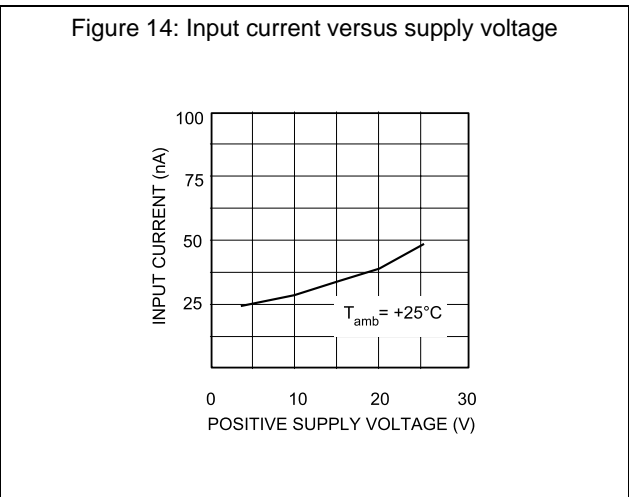
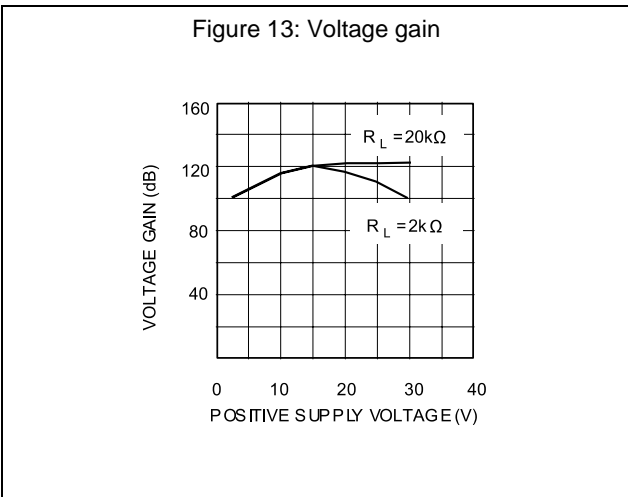
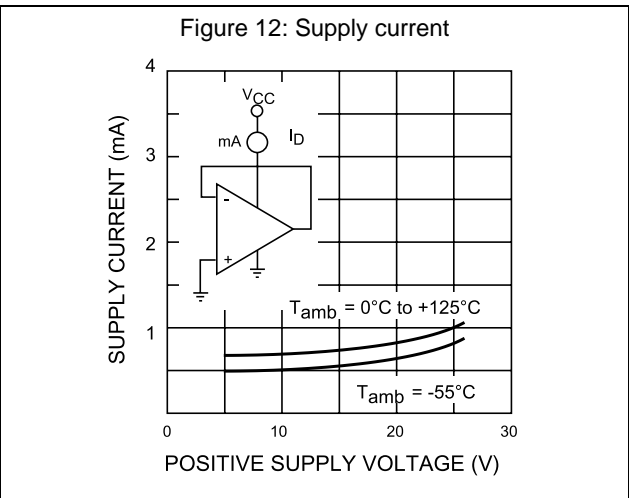
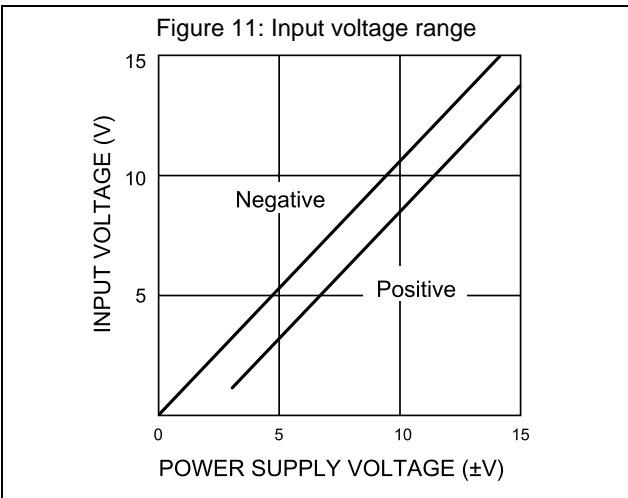
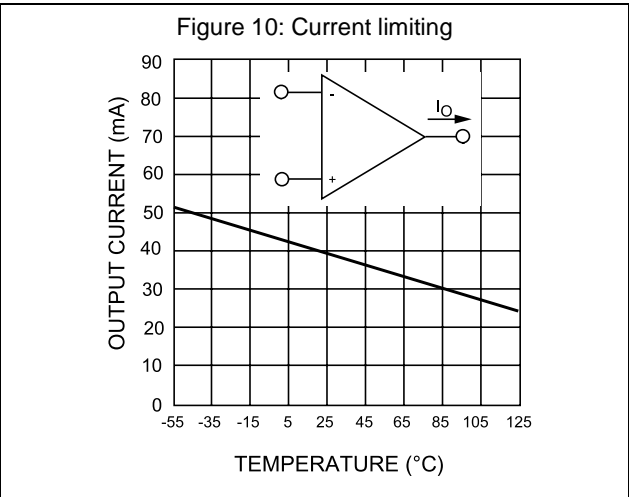
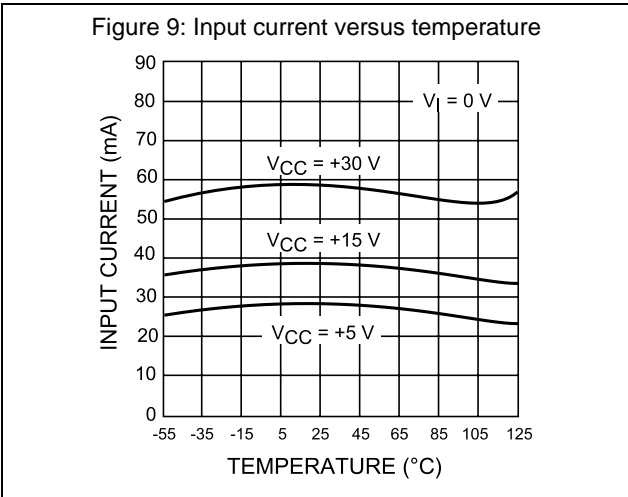


Figure 15: Gain bandwidth product

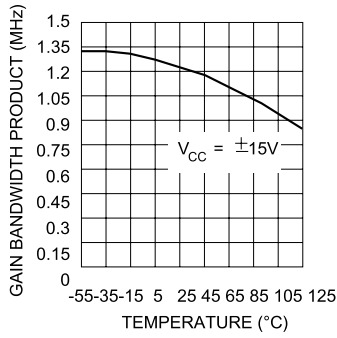


Figure 16: Power supply rejection ratio

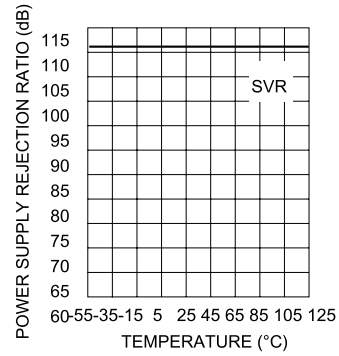


Figure 17: Common-mode rejection ratio

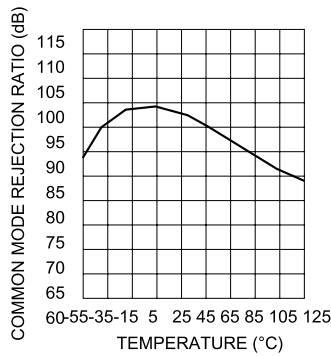
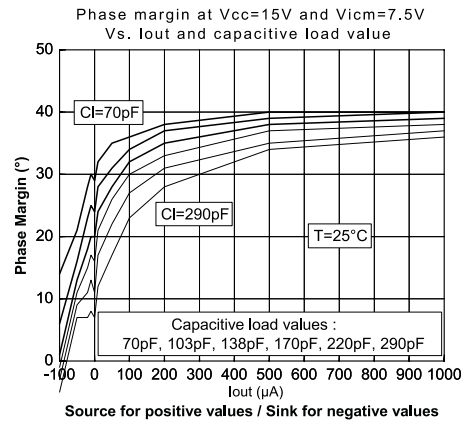


Figure 18: Phase margin vs capacitive load



6 Typical single-supply applications

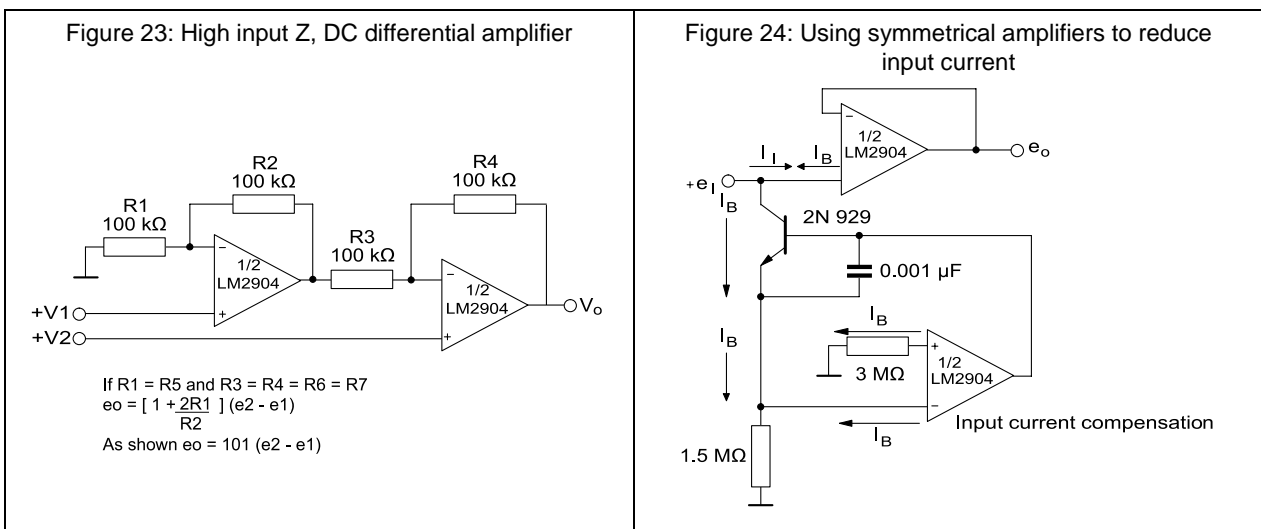
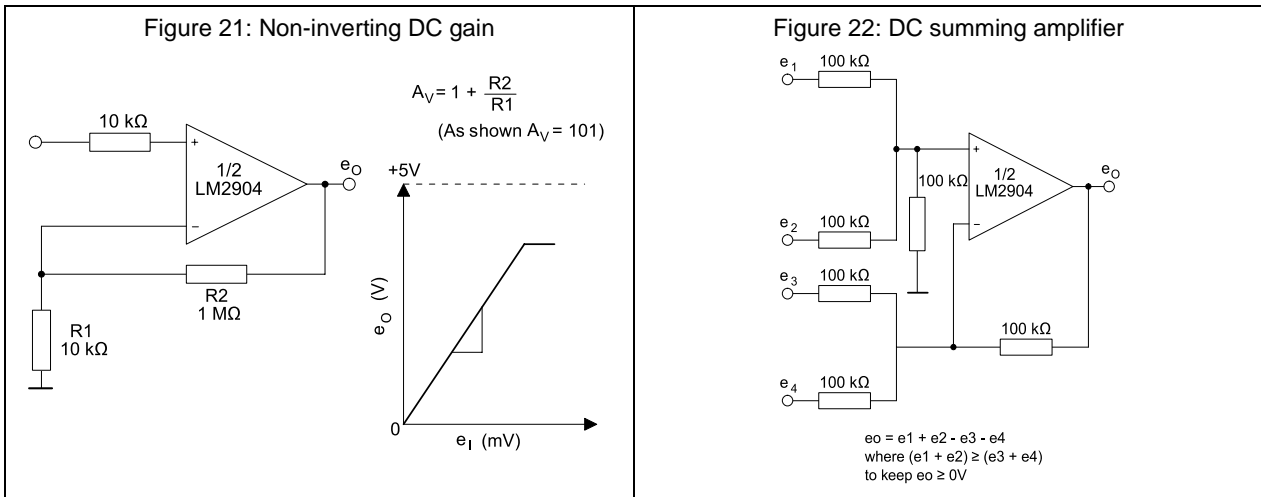
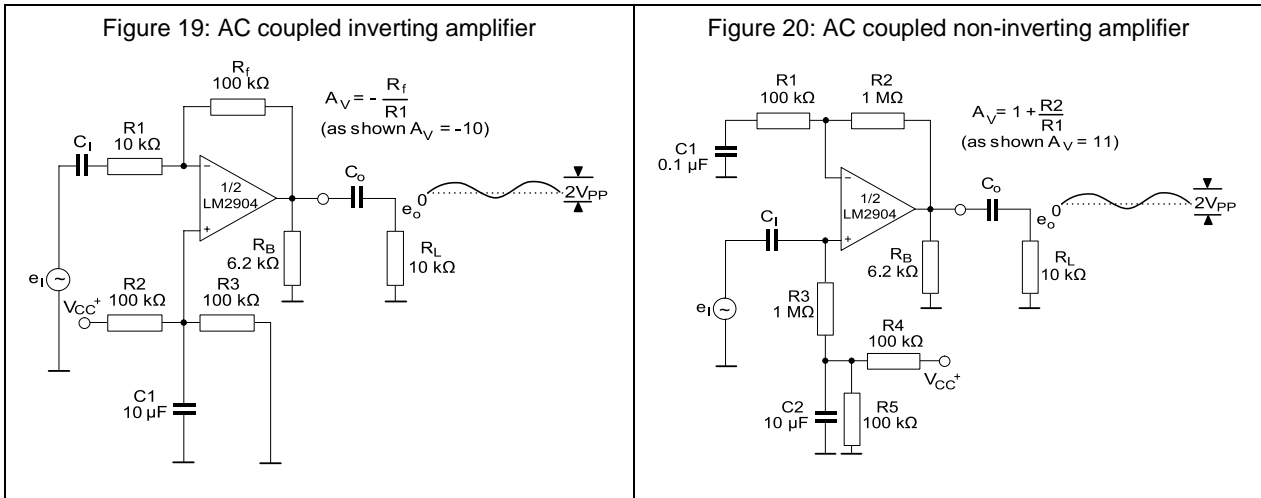


Figure 25: Low drift peak detector

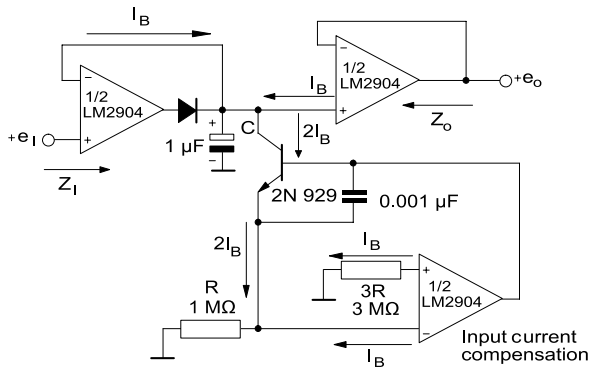
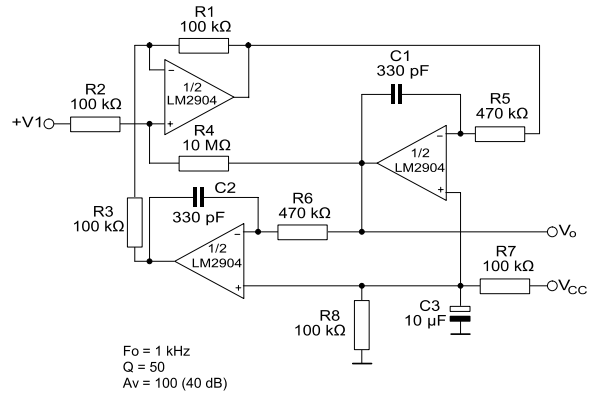


Figure 26: Active bandpass filter



7 Macromodel

An accurate macromodel of the LM2904AH is available on STMicroelectronics' web site at: **www.st.com**. This model is a trade-off between accuracy and complexity (that is, time simulation) of the LM2904AH operational amplifier. It emulates the nominal performances of a typical device within the specified operating conditions mentioned in the datasheet. It also helps to validate a design approach and to select the right operational amplifier, *but it does not* replace on-board measurements.

8 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

8.1 TSSOP8 package information

Figure 27: TSSOP8 package outline

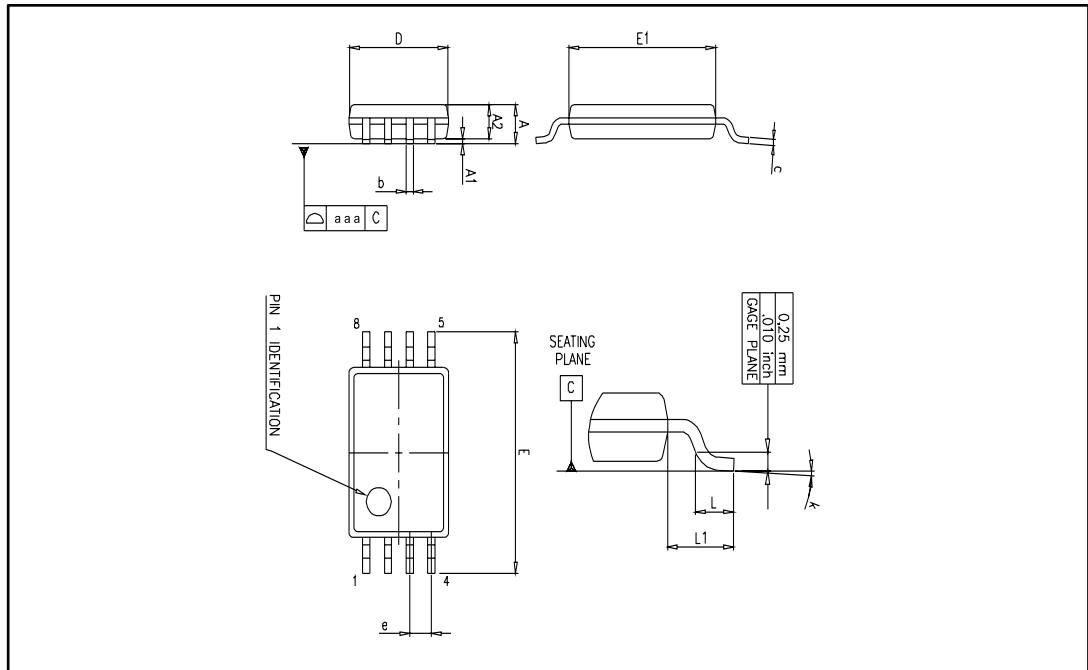


Table 4: TSSOP8 mechanical data

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A			1.2			0.047
A1	0.05		0.15	0.002		0.006
A2	0.80	1.00	1.05	0.031	0.039	0.041
b	0.19		0.30	0.007		0.012
c	0.09		0.20	0.004		0.008
D	2.90	3.00	3.10	0.114	0.118	0.122
E	6.20	6.40	6.60	0.244	0.252	0.260
E1	4.30	4.40	4.50	0.169	0.173	0.177
e		0.65			0.0256	
k	0°		8°	0°		8°
L	0.45	0.60	0.75	0.018	0.024	0.030
L1		1			0.039	
aaa		0.1			0.004	

9 Ordering information

Table 5: Order codes

Order code	Temperature range	Package	Packing	Marking
LM2904AHYPT ⁽¹⁾	-40 °C to 150 °C	TSSOP8 (automotive grade level)	Tape and reel	LM4AH

Notes:

⁽¹⁾Qualified and characterized according to AEC Q100 and Q003 or equivalent, advanced screening according to AEC Q001 and Q002 or equivalent.

10 Revision history

Table 6: Document revision history

Date	Revision	Changes
19-Oct-2015	1	Initial release
05-Nov-2015	2	Updated datasheet layout Table 1: removed T_{oper} parameter Table 3: updated table title
16-Feb-2016	3	Datasheet status changed to "production data" Table 3: unit of V_{OL} parameter changed from "V" to 'mV"
29-Feb-2016	4	Updated product status footnote Table 5 : replaced footnote 1

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